In the Specification:

On page 1, line 9, please delete the "CROSS-REFERENCE TO RELATED APPLICATIONS" and insert the following:

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a continuation of U.S. Patent Application No. 09/387,338, filed August 31, 1999 and now issued as U.S. Patent No. 6,270,647; which is a continuation International Patent Application No. PCT/US98/00126, which was filed in the English language on January 16, 1998; which ~~claims priority from~~ is a continuation of U.S. Patent Application No. 08/940,670, filed September 30, 1997 and U.S. Patent Application No. 08/940,930, filed September 30, 1997.

On page 3, starting at line 9 and continuing through page 4, line 7:

In the electroplating of semiconductor wafers, an anode electrode is disposed in a plating bath and the wafer with the seed layer thereon is used as a cathode with the face of the wafer that is to be plated contacting an upper surface of the plating bath. The semiconductor wafer is held by a support system that also provides requisite cathode potential to the wafer. The support system may comprise conductive fingers that secure the wafer in place and also contact the wafer in order to conduct electrical current for the plating operation.

During the electroplating process, the conductive fingers as well as the semiconductor wafer are plated with the plating metal, such as copper. One potential problem that occurs in such a process is the build up of plating metal deposits on the conductive finger. These deposits may: 1) result in unintended attachment of the conductive finger while in contact with the wafer such that upon disengagement of the conductive finger with the wafer surface, some of the plated surface may tear away and fall off as particles; 2) introduce variability in the current being conducted through the contact and ultimately across the plated surface; and 3) result in small particles breaking off of the deposits on the conductive finger or off of the wafer which may enter the plating bath, and ultimately lodge directly on the wafer surface during plating or contaminate subsequently